

Please add new claim 22 as follows:

22. (New)

A fabrication method of a semiconductor device comprising the steps of:

forming a first insulation layer on a flat underlying face over a substrate,

introducing impurities into said first insulation layer,

forming a trench in said first insulation layer by etching,

embedding and forming a first conductive layer in said first insulation layer,

forming a second insulation layer on said flat first insulation layer and said

flat first conductive layer,

introducing impurities into said second insulation layer,

forming a trench and a contact hole in said first insulation layer by etching,

embedding and forming a second conductive layer in said second insulation

layer.